

**REMARKS**

Claims 1-20 are pending in this application. By this Amendment, the specification is revised to correct typographical errors, and claim 20 is added. Support for new claim 20 is found at, for example, paragraph 15 of the specification.

**I. Priority and Declaration**

Applicants note that priority has been acknowledged. However, the priority documents had not been scanned into the electronic record. Accordingly, Applicants submit herewith a Claim for Priority and certified copy of the priority document.

Furthermore, Applicants submit herewith a Submission of Declaration and Declaration for review and scanning into the electronic record.

**II. Specification Objection**

The specification was objected to for allegedly containing various informalities, including grammatical errors and typographical errors. Accordingly, as requested by the Patent Office, Applicants submit herewith a substitute specification correcting such informalities.

**III. Rejection Under 35 U.S.C. §112, second paragraph**

Claims 12-19 were rejected under 35 U.S.C. §112, second paragraph, as allegedly being indefinite. This rejection is respectfully traversed.

Claim 12 recites a metallic oxide film of high dielectric constant made by the method recited in claim 1. Such method produces a metallic oxide film of high dielectric constant that comprises constituent elements of the substrate mixed with the constituent elements of a given metallic oxide which are grown on the substrate. Namely, the structure of the metallic oxide film of high dielectric constant as achieved by the method comprises an entirely different structure than the  $\text{Pr}_2\text{O}_3$  layer taught by Osten. This feature is described more fully below. Moreover, this distinguishing structure is also now recited in new claim 20.

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